



2716

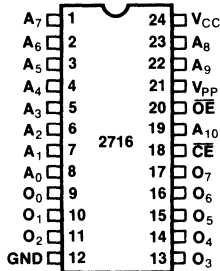
16K (2K x 8) UV ERASABLE PROM

- **Fast Access Time**
 - 2716-1: 350 ns Max.
 - 2716-2: 390 ns Max.
 - 2716: 450 ns Max.
 - 2716-5: 490 ns Max.
 - 2716-6: 650 ns Max.
- **Single +5V Power Supply**
- **Low Power Dissipation**
 - Active Power: 525 mW Max.
 - Standby Power: 132 mW Max.
- **Pin Compatible to Intel 2732A EPROM**
- **Simple Programming Requirements**
 - Single Location Programming
 - Programs with One 50 ms Pulse
- **Inputs and Outputs TTL Compatible During Read and Program**
- **Completely Static**

The Intel 2716 is a 16,384-bit ultraviolet erasable and electrically programmable read-only memory (EPROM). The 2716 operates from a single 5-volt power supply, has a static standby mode, and features fast single-address programming. It makes designing with EPROMs fast, easy and economical.

The 2716, with its single 5-volt supply and with an access time up to 350 ns, is ideal for use with high-performance +5V microprocessors such as Intel's 8085 and 8086. Selected 2716-5s and 2716-6s are also available for slower speed applications. The 2716 also has a static standby mode which reduces power consumption without increasing access time. The maximum active power dissipation is 525 mW while the maximum standby power dissipation is only 132 mW, a 75% savings.

The 2716 uses a simple and fast method for programming—a single TTL-level pulse. There is no need for high voltage pulsing because all programming controls are handled by TTL signals. Programming of any location at any time—either individually, sequentially or at random is possible with the 2716's single-address programming. Total programming time for all 16,384 bits is only 100 seconds.



PIN NAMES

A ₀ -A ₁₀	ADDRESSES
CE	CHIP ENABLE
OE	OUTPUT ENABLE
O ₀ -O ₇	OUTPUTS

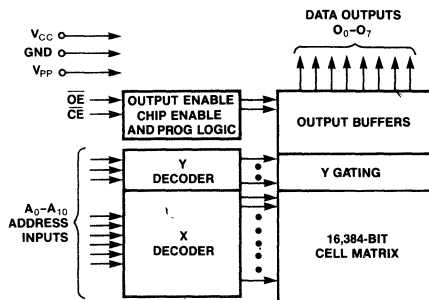


Figure 1. Pin Configuration

Figure 2. Block Diagram

ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias -10°C to +80°C
 Storage Temperature -65°C to +125°C
 All Input or Output Voltages with Respect to Ground +6V to -0.3V
 V_{PP} Supply Voltage with Respect to Ground During Program +26.5V to -0.3V

**NOTICE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

D.C. AND A.C. OPERATING CONDITIONS DURING READ

	2716	2716-1	2716-2	2716-5	2716-6
Temperature Range	0°C–70°C	0°C–70°C	0°C–70°C	0°C–70°C	0°C–70°C
V _{CC} Power Supply ^[1,2]	5V ±5%	5V ±10%	5V ±5%	5V ±5%	5V ±5%
V _{PP} Power Supply ^[2]	V _{CC}	V _{CC}	V _{CC}	V _{CC}	V _{CC}

READ OPERATION

D.C. CHARACTERISTICS

Symbol	Parameter	Limits			Units	Test Conditions
		Min.	Typ. ^[3]	Max.		
I _{LI}	Input Load Current			10	μA	V _{IN} = 5.25V
I _{LO}	Output Leakage Current			10	μA	V _{OUT} = 5.25V
I _{PP1} ^[2]	V _{PP} Current			5	mA	V _{PP} = 5.25V
I _{CC1} ^[2]	V _{CC} Current (Standby)		10	25	mA	$\overline{CE} = V_{IH}, \overline{OE} = V_{IL}$
I _{CC2} ^[2]	V _{CC} Current (Active)		57	100	mA	$\overline{OE} = \overline{CE} = V_{IL}$
V _{IL}	Input Low Voltage	-0.1		0.8	V	
V _{IH}	Input High Voltage	2.0		V _{CC} + 1	V	
V _{OL}	Output Low Voltage			0.45	V	I _{OL} = 2.1 mA
V _{OH}	Output High Voltage	2.4			V	I _{OH} = -400 μA

A.C. CHARACTERISTICS

Symbol	Parameter	Limits (ns)										Test Conditions†
		2716		2716-1		2716-2		2716-5		2716-6		
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t _{ACC}	Address to Output Delay		450		350		390		450		450	$\overline{CE} = \overline{OE} = V_{IL}$
t _{CE}	\overline{CE} to Output Delay		450		350		390		490		650	$\overline{OE} = V_{IL}$
t _{OE} ^[4]	Output Enable to Output Delay		120		120		120		160		200	$\overline{CE} = V_{IL}$
t _{DF} ^[4,6]	\overline{CE} or \overline{OE} High to Output Float	0	100	0	100	0	100	0	100	0	100	$\overline{CE} = V_{IL}$
t _{OH}	Output Hold from Addresses, \overline{CE} or \overline{OE} Whichever Occurred First	0		0		0		0		0		$\overline{CE} = \overline{OE} = V_{IL}$

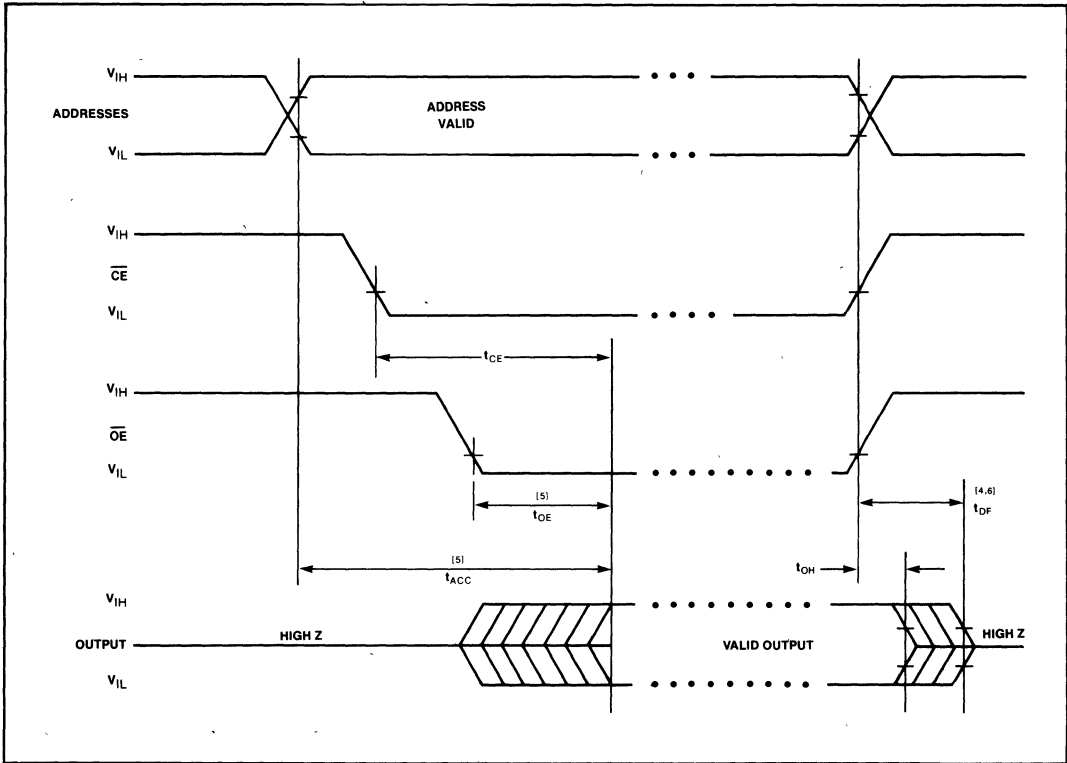
CAPACITANCE^[4] ($T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$)

Symbol	Parameter	Typ. ^[3]	Max.	Units	Test Conditions
C_{IN}	Input Capacitance	4	6	pF	$V_{IN} = 0\text{V}$
C_{OUT}	Output Capacitance	8	12	pF	$V_{OUT} = 0\text{V}$

†A.C. TEST CONDITIONS

Output Load 1 TTL gate and
 $C_L = 100\text{ pF}$
 Input Rise and Fall Times $\leq 20\text{ ns}$
 Input Pulse Levels 0.8V to 2.2V
 Timing Measurement Reference Level:
 Inputs 0.8V and 2V
 Outputs 0.8V and 2V

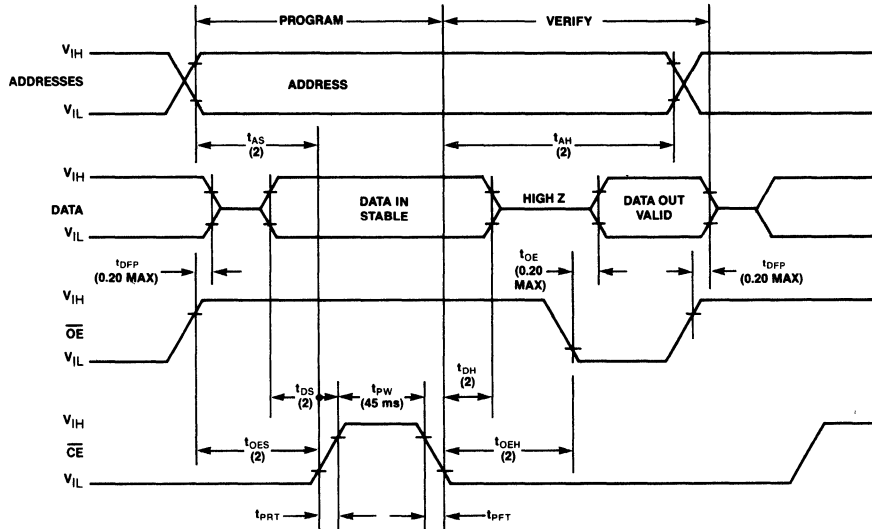
A.C. WAVEFORMS^[1]



NOTES:

1. V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP} .
2. V_{PP} may be connected to V_{CC} except during programming. The supply current would then be the sum of I_{CC} and I_{PP1} .
3. Typical values are for $T_A = 25^\circ\text{C}$ and nominal supply voltages.
4. This parameter is only sampled and is not 100% tested.
5. \overline{OE} may be delayed up to $t_{ACC} - t_{OE}$ after the falling edge of \overline{CE} without impact on t_{ACC} .
6. t_{DF} is specified from \overline{OE} or \overline{CE} , whichever occurs first

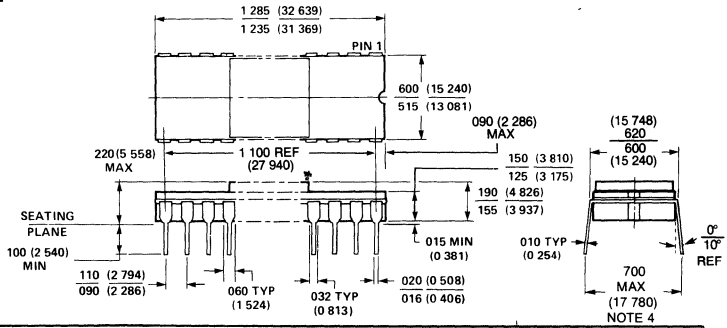
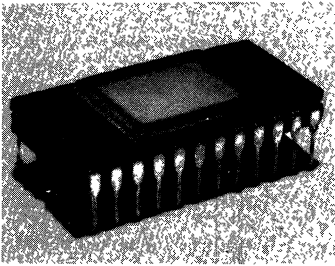
PROGRAMMING WAVEFORMS



NOTE

- 1 ALL TIMES SHOWN IN PARENTHESIS ARE MINIMUM TIMES AND ARE μ SEC UNLESS OTHERWISE NOTED
- 2 t_{OE} AND t_{DFF} ARE CHARACTERISTICS OF THE DEVICE BUT MUST BE ACCOMMODATED BY THE PROGRAMMER

CERAMIC DUAL IN-LINE PACKAGE TYPE B
24-LEAD HERMETIC DUAL IN-LINE
PACKAGE TYPE B



CERAMIC LEADLESS CHIP CARRIERS

18-LEAD CERAMIC LEADLESS
PACKAGE TYPE F

